

Amendments to the Claims:

This listing of claims will replace the listing of claims as pending in the present application:

Listing of Claims:

Claim 1 (original): A silicon carbide epitaxial wafer which is formed on a substrate that is less than 1° off from the {0001} surface of silicon carbide having an α -type crystal structure.

Claim 2 (original): The silicon carbide epitaxial wafer according to claim 1, wherein said silicon carbide epitaxial wafer is formed on a substrate of the {0001} C face.

Claims 3-5 (canceled).

Claim 6 (original): A manufacturing method of a silicon carbide epitaxial wafer, wherein silicon carbide is epitaxially grown on a substrate that is less than 1° off from the {0001} surface of silicon carbide having an α -type crystal structure.

Claim 7 (original): The manufacturing method of a silicon carbide epitaxial wafer according to claim 6, wherein silicon carbide is epitaxially grown on a substrate of the {000 $\bar{1}$ } C face.

Claim 8-15 (canceled).